Silicon NPN Power Transistors 2SC2792

DESCRIPTION

·With TO-3P(I) package
·High breakdown voltage
·Excellent switching times

APPLICATIONS

·Switching regulator and high voltage
·Switching applications
·High speed DC-DC converter applications

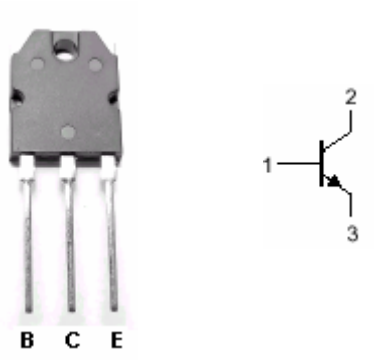

Fig.1 simplified outline (TO-3P(I)) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	850	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current-DC		2	A
I_{CM}	Collector current-peak		4	A
I_B	Base current		1	A
P_T	Total power dissipation	T_C=25□	80	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

Silicon NPN Power Transistors 2SC2792

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ,I_B=0	800			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ,I_E=0	850			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=500mA; I_B=50mA			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=500mA; I_B=50mA			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=800V; I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			1.0	mA
h_{FE}	DC current gain	I_C=0.5A ; V_{CE}=5V	10			
Switching times						
t_r	Rise time	V_{CC}=400V; $2I_{B1}$=-I_{B2}=0.1A; R_L=800Ω			1.0	μs
t_{stg}	Storage time				4.0	μs
t_f	Fall time				1.0	μs

PACKAGE OUTLINE

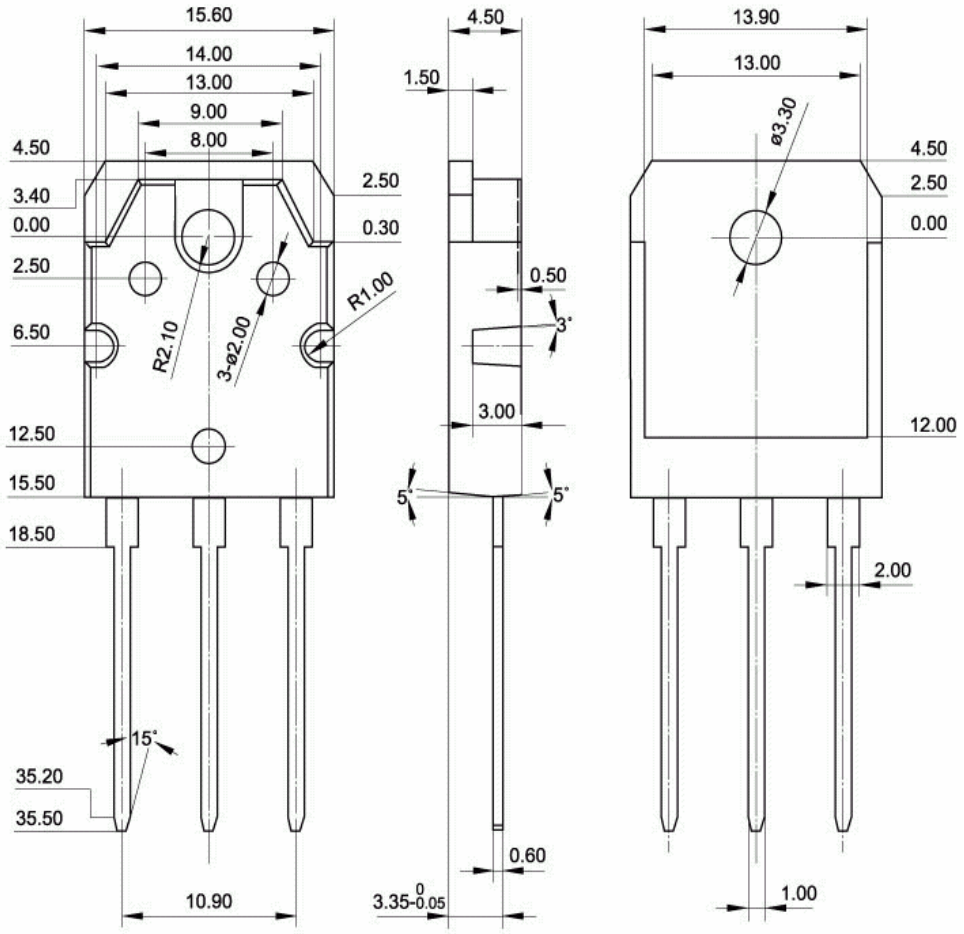

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)

Silicon NPN Power Transistors 2SC2792

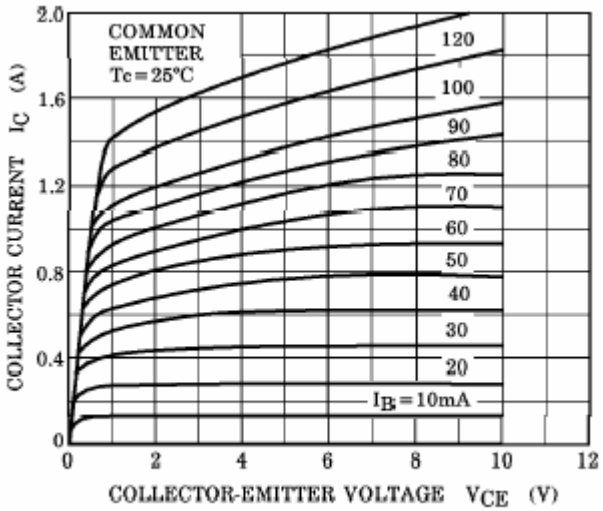

Fig.3 Static Characteristic

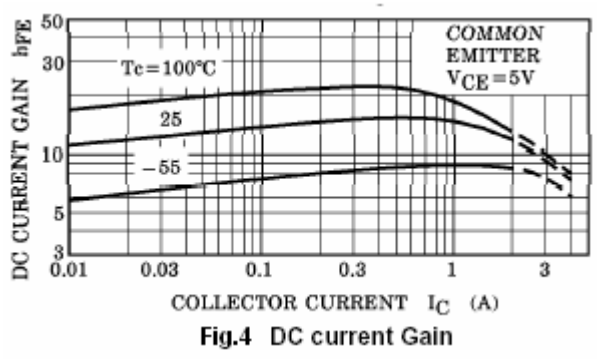

Fig.4 DC current Gain

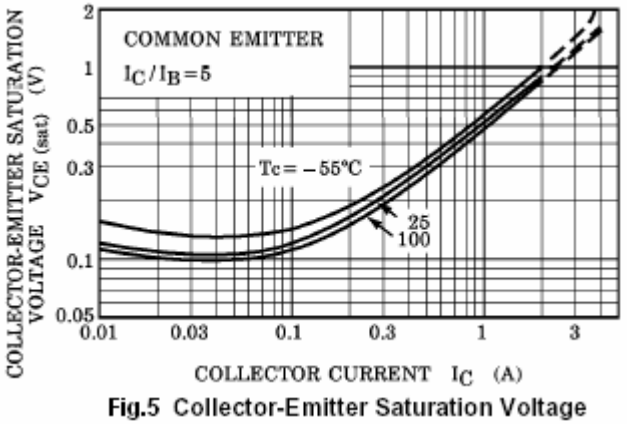

Fig.5 Collector-Emitter Saturation Voltage

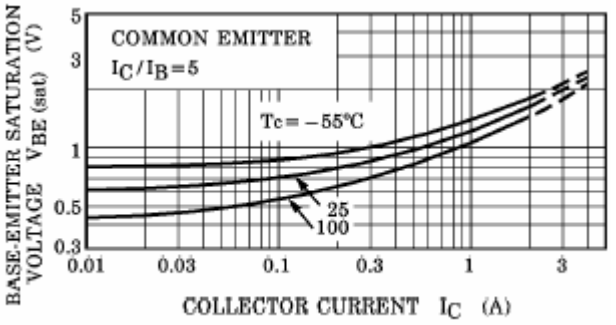

Fig.6 Base-Emitter Saturation Voltage

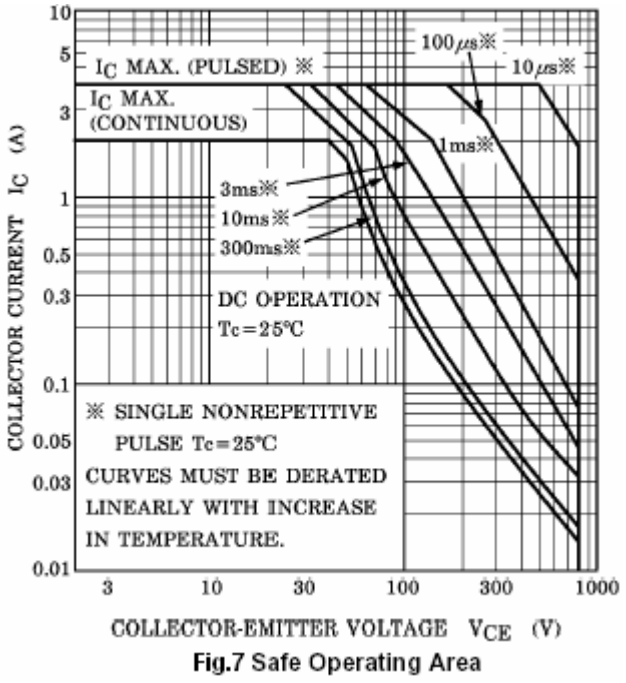

Fig.7 Safe Operating Area